

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device, comprising:
  - a first substrate formed of an insulating material having at least one through hole;
  - a semiconductor element secured to a desired position of a conductive pattern formed on a first main surface of the first substrate;
  - a plurality of electrodes for external connection on a second main surface of the first substrate located opposite to the first main surface of the first substrate that is electrically connected to the desired conductive pattern via the through hole;
  - a resin mold formed so as to cover, at least, the main surfaces of the first substrate,
  - wherein the semiconductor device is characterized in that a second substrate formed of an insulating material having approximately a same coefficient of linear expansion as the first substrate is adhered to the second main surface of the first substrate so that, at least, the electrodes are exposed; and
  - wherein a portion of the second substrate passes between at least two of the electrodes and extends from the second main surface at least as far as the electrodes extend from the second main surface.
2. (Currently Amended) The semiconductor device according to Claim 1, ~~characterized in that~~ wherein the second substrate is adhered to the first substrate so that, at least, the sides of the electrodes located in the vicinity of outer sides of the second main surface of the first substrate are exposed from the outer sides.

3. (Currently Amended) The semiconductor device according to Claim 1, ~~characterized~~  
~~in that~~ wherein the second substrate separates the electrodes from each other so that the  
electrodes exist independently in separate regions.

4. (Currently Amended) The semiconductor device according to Claim 2, ~~characterized~~  
~~in that~~ wherein the second substrate is thicker than the electrodes for external connection.

5. (Currently Amended) The semiconductor device according to Claim 2, ~~characterized~~  
~~in that~~ wherein the electrodes are plated with gold.

6. (Currently Amended) The semiconductor device according to Claim 2, ~~characterized~~  
~~in that~~ wherein the first and second substrates are ceramic substrates.

7. (Currently Amended) The semiconductor device according to Claim 2, ~~characterized~~  
~~in that~~ wherein the second substrate separates the electrodes from each other so that the  
electrodes exist independently in separate regions.

8. (Currently Amended) The semiconductor device according to Claim 3, ~~characterized~~  
~~in that~~ wherein the second substrate is thicker than the electrodes.

9. (Currently Amended) The semiconductor device according to Claim 3, ~~characterized~~  
~~in that~~ wherein the electrodes are plated with gold.

10. (Currently Amended) The semiconductor device according to Claim 3, ~~characterized~~  
~~in that~~ wherein the first and second substrates are ceramic substrates.

11. (Currently Amended) The semiconductor device according to claim 1, comprising a  
metal wire to electrically connect an electrode pad of the semiconductor element to the desired  
conductive pattern.

12. (Currently Amended) A method for forming a semiconductor device, comprising:  
adhering a second substrate to a second surface of a first substrate;  
subsequently mounting a semiconductor element on a first surface of the first substrate;  
and

electrically coupling the semiconductor element to one or more electrodes on the second  
surface of the first substrate,

wherein the electrodes are exposed;

wherein adhering the second substrate comprises positioning the second substrate such  
that a portion of the second substrate passes between at least two of the electrodes and extends  
from the second surface at least as far as the electrodes extend from the second surface.

13. (Previously presented) The method of claim 12, wherein a thickness of the second  
substrate is greater than a thickness of the electrode.

14. (Previously presented) The method of claim 12, wherein a coefficient of expansion  
of the first substrate and a coefficient of expansion of the second substrate are substantially  
equal.

15. (New) The semiconductor device according to claim 1, wherein the portion of the  
second substrate extends from the second main surface farther than the electrodes extend from  
the second main surface.

16. (New) The semiconductor device according to claim 1, wherein the second main  
surface defines an outer periphery thereof and wherein each terminal is exposed at the second  
main surface at a position that is a distance inside the outer periphery.

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17. (New) The semiconductor device according to claim 16, wherein the distance is between approximately 0.05 mm and 0.1 mm.